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(21)Application number : 03-159601 (71)Applicant : SONY CORP

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(54) SOLID STATE IMAGE SENSOR

(57)Abstract:

PURPOSE: To improve sensitivity by optimizing I-V characteristics of MOS transistors of drive and load sides and maximizing an AC gain at the time of a small signal of a source follower amplifier.

CONSTITUTION: In a CCD solid state image sensor having a floating diffusion type charge detecting amplifier as an output unit, a P-well 19 of a drive side MOS transistor 8 and a P-well 20 of a load side MOS transistor 9 are formed independently in such a manner that the P-well 19 is formed to be deep and the P-well 20 is formed to be shallow from the surface of a substrate 11 and to be neutralized at a potential.

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